BT137S series D BT137M series D

GENERAL DESCRIPTION

Glass passivated, sensitive gate triacs in a plastic envelope, suitable for surface mounting, intended for use in general purpose bidirectional switching and phase control applications. These devices are intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

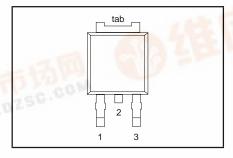
QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	MAX.	UNIT
V _{DRM} I _{T(RMS)} I _{TSM}	BT137S (or BT137M)- Repetitive peak off-state voltages RMS on-state current Non-repetitive peak on-state current	500D 500 8 65	600D 600 8 65	V A A

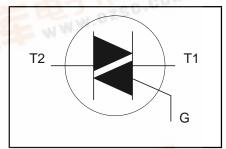
PINNING - SOT428

PIN NUMBER	Standard S	Alternative M		
1	MT1	gate		
2	MT2	MT2		
3	gate	MT1		
tab	MT2	MT2		

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

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SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.		UNIT
V _{DRM}	Repetitive peak off-state voltages	THE PROPERTY		-500 500 ¹	-600 600 ¹	V
I _{T(RMS)} I _{TSM}	RMS on-state current Non-repetitive peak on-state current	full sine wave; T _{mb} ≤ 102 °C full sine wave; T _j = 25 °C prior to surge	-	8		А
	FET I.	t = 20 ms t = 16.7 ms	-	6 7		A
l ² t	I ² t for fusing	t = 10.7 ms	_	2		A A ² s
dl _⊤ /dt	Repetitive rate of rise of on-state current after	$I_{TM} = 12 \text{ A}; I_G = 0.2 \text{ A}; \\ dI_G/dt = 0.2 \text{ A}/\mu\text{s}$	-	由子		N.
	triggering	T2+ G+ T2+ G- T2- G- T2- G+	15	5	0 0 0 0	Α/μs Α/μs Α/μs Α/μs
$egin{array}{c} I_{GM} \ V_{GM} \ P_{GM} \end{array}$	Peak gate current Peak gate voltage Peak gate power	ZSC.COM	- - -	2	2	V W
P _{G(AV)} T _{stg}	Average gate power Storage temperature Operating junction temperature	over any 20 ms period	- -40 -	15	.5 50 25	ο̈́ο

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THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
R _{th j-mb}	Thermal resistance junction to mounting base	full cycle half cycle	-	-	2.0 2.4	K/W K/W
R _{th j-a}	Thermal resistance junction to ambient	pcb (FR4) mounted; footprint as in Fig.14	-	75	-	K/W

STATIC CHARACTERISTICS

T_i = 25 °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{GT}	Gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}$				
		T2+ G+	-	2.5	5	mA
		T2+ G-	-	3.5	5	mA
		T2- G-	-	3.5	5	mA
		T2- G+	-	6.5	10	mA
I _L	Latching current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$				
		T2+ G+	-	1.6	15	mA
		T2+ G-	-	8.5	20	mA
		T2- G-	-	1.2	15	mA
		T2- G+	-	2.5	20	mA
I _H	Holding current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$	-	1.5	10	mA
V_{T}	On-state voltage	$ I_{T} = 10 \text{ A}$	-	1.3	1.65	V
V _{GT}	Gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}$	-	0.7	1.5	V
		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_i = 125 ^{\circ}\text{C}$	0.25	0.4	-	V
I_{D}	Off-state leakage current	$V_D = V_{DRM(max)}$; $T_j = 125 ^{\circ}C$	-	0.1	0.5	mA

DYNAMIC CHARACTERISTICS

 $T_i = 25$ °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
dV _D /dt	Critical rate of rise of off-state voltage	V_{DM} = 67% $V_{DRM(max)}$; T_j = 125 °C; exponential waveform; R_{GK} = 1 kΩ	-	5	1	V/μs
t _{gt}	Gate controlled turn-on time	$I_{TM} = 12 \text{ A}; V_D = V_{DRM(max)}; I_G = 0.1 \text{ A};$ $dI_G/dt = 5 \text{ A}/\mu\text{s}$	-	2	-	μs

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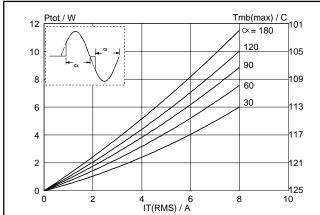


Fig.1. Maximum on-state dissipation, P_{tot} , versus rms on-state current, $I_{T(RMS)}$, where α = conduction angle.

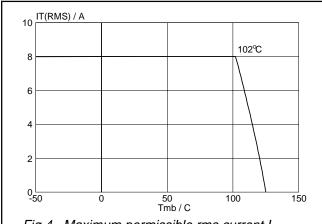


Fig.4. Maximum permissible rms current $I_{T(RMS)}$, versus mounting base temperature T_{mb} .

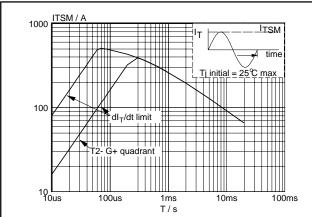


Fig.2. Maximum permissible non-repetitive peak on-state current I_{TSM} , versus pulse width t_p , for sinusoidal currents, $t_p \le 20$ ms.

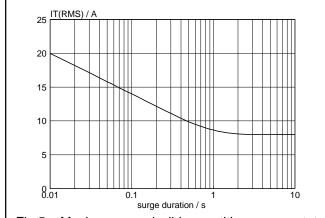


Fig.5. Maximum permissible repetitive rms on-state current $I_{T(RMS)}$, versus surge duration, for sinusoidal currents, f = 50 Hz; $T_{mb} \le 102$ °C.

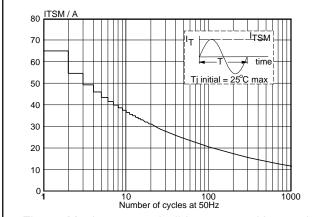


Fig.3. Maximum permissible non-repetitive peak on-state current I_{TSM} , versus number of cycles, for sinusoidal currents, f = 50 Hz.

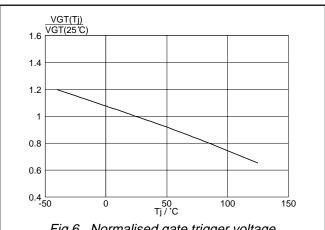
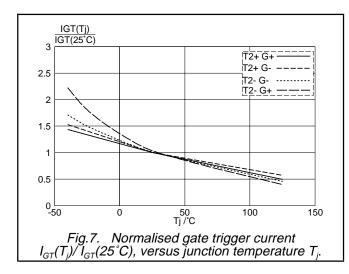
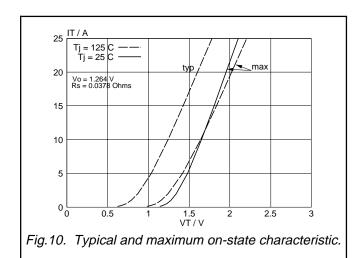
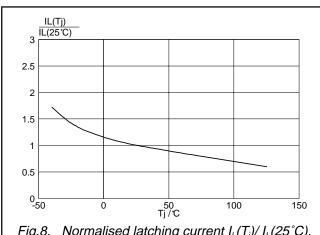


Fig.6. Normalised gate trigger voltage $V_{GT}(T_j)/V_{GT}(25^{\circ}C)$, versus junction temperature T_j .

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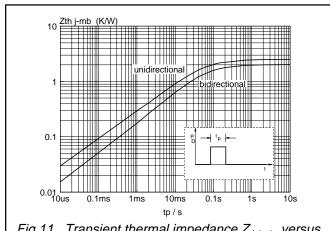
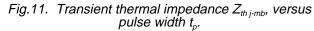
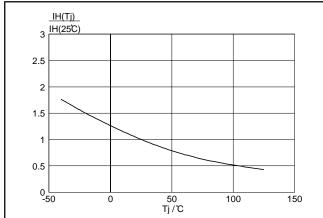


Fig.8. Normalised latching current $I_L(T_i)/I_L(25^{\circ}C)$, versus junction temperature T_i .





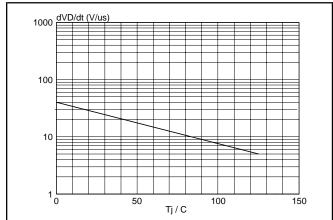


Fig.9. Normalised holding current $I_H(T_i)/I_H(25^{\circ}C)$, versus junction temperature T_i .

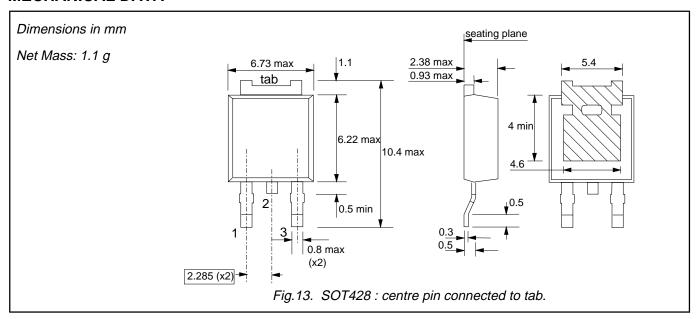
Fig.12. Typical, critical rate of rise of off-state voltage, dV_D/dt versus junction temperature T_j .

Philips Semiconductors Product specification

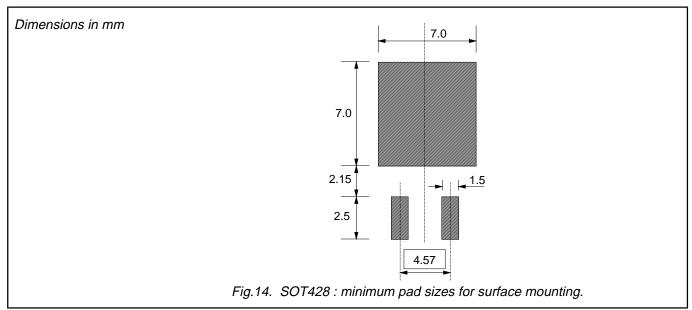
Triacs logic level

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MECHANICAL DATA



MOUNTING INSTRUCTIONS



Notes

1. Plastic meets UL94 V0 at 1/8".

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DEFINITIONS

Data sheet status					
Objective specification	This data sheet contains target or goal specifications for product development.				
Preliminary specification This data sheet contains preliminary data; supplementary data may be published					
Product specification This data sheet contains final product specifications.					
1.1.1/1					

Limiting values

Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information

Where application information is given, it is advisory and does not form part of the specification.

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